

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Canceled)
5. (Canceled)
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Canceled)
10. (Canceled)
11. (Canceled)
12. (Canceled)
13. (Canceled)
14. (Canceled)
15. (Canceled)
16. (Canceled)
17. (Canceled)
18. (Canceled)
19. (Canceled)
20. (Canceled)
21. (Canceled)
22. (Canceled)

23. (Canceled)

24. (Canceled)

25. (Canceled)

26. (Canceled)

DI 27. (Previously Amended) An etching mask for selectively etching a workpiece, wherein the etching mask is made of a metal and has a cross-sectional shape comprising a rectangular first region that determines a pattern width of the workpiece, and a second region that contacts the first region and intercepts application of etching beams to a sidewall of the first region during etching.

28. (Previously Amended) An etching mask for selectively etching a workpiece, wherein the etching mask is made of a metal and has a cross-sectional shape comprising a rectangular first region that determines a pattern width of the workpiece, and a second region that intercepts application of etching beams to a sidewall of the first region during etching, wherein the etching mask has a T-shaped cross section.

29. (Previously Added) The etching mask according to claim 28, comprising a cross section including a vertical bar having an end that contacts with a surface of the workpiece, and a lateral bar placed on another end of the vertical bar and having a width greater than a width of the vertical bar, wherein a pattern width of the workpiece is determined by the width of the vertical bar.

30. (Previously Amended) An etching mask for selectively etching a workpiece, wherein the etching mask is made of a metal and has a cross-sectional shape comprising a rectangular first region that determines a pattern width of the workpiece, and a second region that intercepts application of etching beams to a sidewall of the first region during etching, wherein the first region is a vertical bar having an end that contacts with a surface of the workpiece, and the second region is a lateral bar placed on another end of the vertical bar and

having a width greater than a width of the vertical bar, wherein a pattern width of the workpiece is determined by the width of the vertical bar.

31. (Previously Added) The etching mask according to claim 28, wherein the metal is selected from the group consisting of NiFe, NiB, NiP, Cu, Au and an alloy comprising one of Co and Ta.

32. (Previously Added) The etching mask according to claim 27, wherein the metal is selected from the group consisting of NiFe, NiB, NiP, Cu, Au and an alloy comprising one of Co and Ta.

33. (Canceled)

34. (Canceled)

35. (Canceled)

36. (Canceled)

37. (Canceled)

38. (New) An etching mask for selectively etching a workpiece, wherein the etching mask is made of a metal and has a cross-sectional shape comprising a rectangular first region that determines a pattern width of the workpiece and a second region that contacts the first region and intercepts application of etching beams to a sidewall of the first region during etching, wherein the first region has a first height and a first width and the second region has a second height and a second width, and wherein the second width is greater than the first width and first height is greater than the second height.

39. (New) An etching mask for selectively etching a workpiece, wherein the etching mask is made of a metal and has a cross-sectional shape comprising a rectangular first region that determines a pattern width of the workpiece and a second region that intercepts application of etching beams to a sidewall of the first region during etching, wherein the etching mask has a T-shaped cross section, wherein the first region has a first height and a

first width and the second region has a second height and a second width, and wherein the second width is greater than the first width and first height is greater than the second height.

40. (New) The etching mask of claim 38 wherein the second region continuously contacts the first region along the first width of the first region.

DI 41. (New) The etching mask of claim 39 wherein the second region continuously contacts the first region along the first width of the first region.

42. (New) The etching mask of claim 30 wherein the vertical bar continuously contacts the lateral bar along the entire width of the vertical bar.

43. (New) The etching mask according to claim 30, wherein the metal is selected from the group consisting of NiFe, NiB, NiP, Cu, Au and an alloy comprising one of Co and Ta.

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